

HiPerFET™ Power MOSFETs

Single MOSFET Die

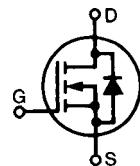
Avalanche Rated

Preliminary data sheet

IXFK 34N80 IXFX 34N80

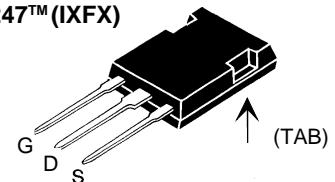
V_{DSS} = 800 V
 I_{D25} = 34 A
 $R_{DS(on)}$ = 0.24 Ω

$t_{rr} \leq 250$ ns

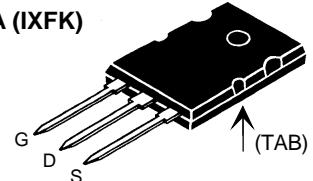


Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800		V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	800		V
V_{GS}	Continuous	± 20		V
V_{GSM}	Transient	± 30		V
I_{D25}	$T_c = 25^\circ\text{C}$	34		A
I_{DM}	$T_c = 25^\circ\text{C}$, pulse width limited by T_{JM}	136		A
I_{AR}	$T_c = 25^\circ\text{C}$	36		A
E_{AR}	$T_c = 25^\circ\text{C}$	64		mJ
E_{AS}	$T_c = 25^\circ\text{C}$	3		J
dv/dt	$I_s \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2\Omega$	5		V/ns
P_D	$T_c = 25^\circ\text{C}$	560		W
T_J		-55 ... +150		°C
T_{JM}		150		°C
T_{stg}		-55 ... +150		°C
T_L	1.6 mm (0.063 in.) from case for 10 s	300		°C
M_d	Mounting torque	TO-264	0.9/6	Nm/lb.in.
Weight	PLUS 247 TO-264	6 10	g	g

PLUS 247™(IXFX)



TO-264 AA (IXFK)



G = Gate
S = Source

D = Drain
TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

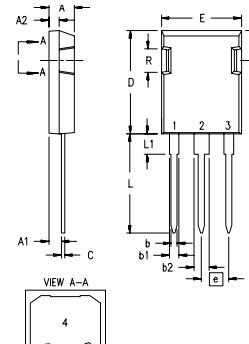
Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0$			$\pm 200\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Note 1			0.24 Ω

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
g_{fs}	$V_{DS} = 10 \text{ V}; I_D = 0.5 \cdot I_{D25}$ Note 1	20	35	S	
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	7500	pF		
		920	pF		
		220	pF		
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1 \Omega$ (External),	45	ns		
		45	ns		
		100	ns		
		40	ns		
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$	270	nC		
		60	nC		
		140	nC		
R_{thJC}		0.22	K/W		
R_{thCK}		0.15	K/W		

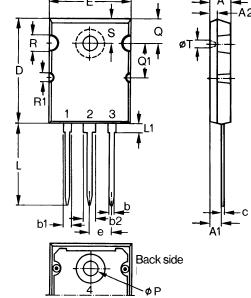
Source-Drain Diode

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
I_s	$V_{GS} = 0 \text{ V}$		34	A	
I_{SM}	Repetitive; pulse width limited by T_{JM}		136	A	
V_{SD}	$I_F = I_s, V_{GS} = 0 \text{ V}$, Note 1		1.5	V	
t_{rr} Q_{RM} I_{RM}	$I_F = I_s, -di/dt = 100 \text{ A}/\mu\text{s}, V_R = 100 \text{ V}$		250	ns	
			1.4	μC	
			10	A	

Note: 1. Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$
 2. See characterization curves in datasheet IXFN34N80.

PLUS247™ (IXFX) Outline


Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45	BSC	.215	BSC
L	19.81	20.32	.780	.800
L ₁	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

TO-264 AA Outline


Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.82	5.13	.190	.202
A ₁	2.54	2.89	.100	.114
A ₂	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b ₁	2.39	2.69	.094	.106
b ₂	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46	BSC	.215	BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L ₁	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q ₁	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R ₁	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072



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